NSN 5961-01-212-8013



Transistor - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-01-212-8013 **Inclosure Material:** Metal **Overall Length:** 0.210 inches **Terminal Length:** 0.500 inches **Overall Diameter:** 0.230 inches **End Application:** Satellite communications set, an/wsc- (v) 9 **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Internal Junction Configuration:** Npn **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 30.0 breakdown voltage, collector-to-base, emitter open and 15.0 breakdown voltage, collector-to-emitter, base open and 3.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 50.00 milliamperes collector current, dc **Power Rating Per Characteristic:** 200.0 milliwatts total power dissipation **Transfer Ratio:** 20.0 small-signal short-circuit forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Terminal Type And Quantity:** 4 uninsulated wire lead Shelf Life:

No

Unit Of Measure:

Demilitarization:

N/a

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